

PRODUCT / PROCESS CHANGE NOTIFICATION

1. PCN basic data

1.1 Company	 STMicroelectronics International N.V
1.2 PCN No.	POWER AND DISCRETES/26/16543
1.3 Title of PCN	HU3PAK SiC MOSFET Gen 3 Back End introduction at Bouskoura (BSK) _ Morocco on top of the actual ATJ JAPAN on new 8 inches Front End FAB (CW8F – SiC Campus)
1.4 Product Category	Pls refer to the impacted products list.
1.5 Issue date	2026-08-10

2. PCN Team

2.1 Contact supplier	
2.1.1 Name	PIKE EMMA
2.1.2 Phone	+44 1628896111
2.1.3 Email	emma.pike@st.com
2.2 Change responsibility	
2.2.1 Product Manager	Angelo RAO
2.1.2 Marketing Manager	Francesco FISICHELLA
2.1.3 Quality Manager	Massimiliano CUOZZO

3. Change

3.1 Category	3.2 Type of change	3.3 Manufacturing Location
Transfer	Product transfer from one site to another site, even if test or process line is qualified	- CW8F/SiC Campus as Front End Plant - BSK/Marocco and ATJ/Japan as Back End Plants

4. Description of change

	Old	New
4.1 Description	- CTWF/Catania FE 6" as Front End Plant - ATJ/Japan as Back End Plant	- CW8F/SiC Campus as Front End Plant - BSK/Marocco and ATJ/Japan as Back End Plants
4.2 Anticipated Impact on form,fit, function, quality, reliability or processability?	No Impact	

5. Reason / motivation for change

5.1 Motivation	Capacity Extension
5.2 Customer Benefit	SERVICE CONTINUITY

6. Marking of parts / traceability of change

6.1 Description	by FGs
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7. Timing / schedule

7.1 Date of qualification results	2026-12-22
7.2 Intended start of delivery	2027-01-08
7.3 Qualification sample available?	Upon Request

8. Qualification / Validation

8.1 Description			
8.2 Qualification report and qualification results	In progress	Issue Date	

9. Attachments (additional documentations)

16543 Public product.pdf
16543 HU3PAK - BSK Back End introduction in CW8F Sic Campus manufacturing location.pdf
16543 HU3PAK_BSK BE introduction WSIC 8_Rev3.pdf

10. Affected parts		
10. 1 Current		10.2 New (if applicable)
10.1.1 Customer Part No	10.1.2 Supplier Part No	10.1.2 Supplier Part No
4632676	SCT011HU75G3AG	
4740489	SCT018HU65G3AG	
4729014	SCT019HU120G3AG	
4632678	SCT020HU120G3AG	

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Public Products List

Public Products are off the shelf products. They are not dedicated to specific customers, they are available through ST Sales team, or Distributors, and visible on ST.com

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PCN Reference : POWER AND DISCRETES/26/16543

Subject : Public Products List

Dear Customer,

Please find below the Standard Public Products List impacted by the change.

SCT055HU65G3AG	SCT020HU120G3AG	SCT027HU65G3AG
SCT011HU75G3AG	SCT025HU120G3AG	SCT019HU120G3AG
SCT018HU65G3AG		

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 new 8 inches Front End FAB (CW8F – SiC Campus)

POWER AND DISCRETES/26/16543

Product family	Technology	Package
SiC MOSFET	Gen 3	HU3PAK

Description of the change

Dear Customer,

Following the continuous improvement of our service and in order to increase the productivity, this document is announcing that SiC MOSFETs, listed in this PCN, diffused at 8 inches CW8F SiC Campus and assembled in HU3PAK package at ATJ-Japan Plant, will be also assembled in Bouskoura (BSK) – Morocco ST Plant.

HU3PAK SiC MOSFETs produced in BSK guarantees the same quality and performance as per current production.

BSK is a Back-End manufacturing facility that has been extensively utilized to produce ST IGBT, High-Voltage Silicon MOSFET, and Silicon Carbide custom products for several years.

The involved products are listed in the table below:

CP
SCT016HU120G3AG
SCT019HU120G3AG
SCT020HU120G3AG
SCT025HU120G3AG
SCT011HU75G3AG
SCT018HU65G3AG
SCT027HU65G3AG
SCT055HU65G3AG

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POWER AND
DISCRETES/26/16543**Reason**

Capacity extension / service improvement

Date of implementationStarting from Jan, 8th 2027**Qualification of the change**

See attached Qualification Plan

Marking and traceability:

Unless otherwise stated by customer specific requirement, traceability of products assembled in BSK - Morocco will be ensured by Finished Good.

*Sincerely Yours.**Catania, August 7th, 2026*

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HU3PAK_BSK BE introduction WSIC 8” for GEN3 Technology Reliability Plan

Analog, Power & Discrete, MEMS & Sensors Group

Quality & Reliability

July 2026

Reliability Plan Strategy

In the next slides we reported the reliability plan for the HU3PAK Package to be introduced at ST Bouskoura assembly plant

- The product will be qualified according to the latest international guideline AEC-Q101 rev.E, and ST internal specification #0061692
- Three different diffusion lots are required for the master test vehicles and delta reliability matrix on one lot for lower representative Voltage class.
- The strategy is based on the following:
 - BRFGA1 was defined as Master for SiC GEN3 650V technology,
 - BVJJA1 and BVJ7A1 were define as Master (lot combined) for SiC GEN3 1200V technology
 - BRGNA1 chosen to cover for SiC GEN3 750V voltage class technology with delta reliability matrix.

Involved products

CP	Product Line	PACKAGE
SCT016HU120G3AG	BRJNA2	HU3PAK
SCT019HU120G3AG	BRIGA1	HU3PAK
SCT020HU120G3AG	BRJJA1-BVJJA1	HU3PAK
SCT025HU120G3AG	BRICA1	HU3PAK
SCT011HU75G3AG	BRGNA1	HU3PAK
SCT018HU65G3AG	BRFCA1	HU3PAK
SCT027HU65G3AG	BRF9A1	HU3PAK
SCT055HU65G3AG	BRF5A1	HU3PAK

Trials detail

Reliability Test Item	Test Condition	BRIGA1	BRJNA2	BVJJA1	BRICA1	BRGNA1	BRFCA1	BRF9A1	BRF5A1
Parametric Verification	All parameters according to user specification	25 x 1 Lots	25 x 1 Lots	25 x 2 lot	25 x 1 lot	25 x 3 Lots	25 x 1 lot	25 x 1 lot	25 x 1 lot
Preconditioning	24h bake@125°C MSL1: 168h moisture soak @ TA=85°C, RH=85% 3x Reflow simulation with Peak Reflow Temp= 245°C	Fam.Data BVJJA1 + BVJ7A1	Fam.Data BVJJA1 + BVJ7A1	ALL parts submitted to TC, IOL, H3TRB and AC	Fam.Data BVJJA1 + BVJ7A1	ALL parts submitted to IOL and H3TRB	Fam.Data BRFGA1	Fam.Data BRFGA1	Fam.Data BRFGA1
HTRB	1000h @ Ta=175°C, Vds= 750V	Fam.Data BVJJA1 + BVJ7A1	Fam.Data BVJJA1 + BVJ7A1	77 x 2 Lots + Fam.Data BVJ7A1	Fam.Data BVJJA1 + BVJ7A1	77 x 3 Lots	Fam.Data BRFGA1	Fam.Data BRFGA1	Fam.Data BRFGA1
HTGB	HTGB+ Tj=175°C, Vgs= 22V, 1000h	Fam.Data BVJJA1 + BVJ7A1	Fam.Data BVJJA1 + BVJ7A1	77 x 2 Lots + Fam.Data BVJ7A1	Fam.Data BVJJA1 + BVJ7A1	77 x 3 Lots	Fam.Data BRFGA1	Fam.Data BRFGA1	Fam.Data BRFGA1
	HTGB- Tj=175°C, Vgs= -10V, 1000	Fam.Data BVJJA1 + BVJ7A1	Fam.Data BVJJA1 + BVJ7A1	77 x 2 Lots + Fam.Data BVJ7A1	Fam.Data BVJJA1 + BVJ7A1	77 x 3 Lots	Fam.Data BRFGA1	Fam.Data BRFGA1	Fam.Data BRFGA1
TC	Ta=-55°C /+150°C Duration= 1000cy	Fam.Data BVJJA1 + BVJ7A1	Fam.Data BVJJA1 + BVJ7A1 + BRGNA1	77 x 2 Lots + Fam.Data BVJ7A1	Fam.Data BVJJA1 + BVJ7A1	77 x 3 Lots	Fam.Data BRFGA1	Fam.Data BRFGA1	Fam.Data BRFGA1
AC	Autoclave (Ta=121°C, Pa=2atm for 96 hours)	Fam.Data BVJJA1 + BVJ7A1	Fam.Data BVJJA1 + BVJ7A1 + BRGNA1	77 x 2 Lots + Fam.Data BVJ7A1	Fam.Data BVJJA1 + BVJ7A1	77 x 3 Lots	Fam.Data BRFGA1	Fam.Data BRFGA1	Fam.Data BRFGA1
HV H3TRB	1000h @ Ta=85°C, RH=85% 80% Vdsmax	Fam.Data BVJJA1 + BVJ7A1	Fam.Data BVJJA1 + BVJ7A1 + BRGNA1	77 x 2 Lots + Fam.Data BVJ7A1	Fam.Data BVJJA1 + BVJ7A1	77 x 3 Lots	Fam.Data BRFGA1	Fam.Data BRFGA1	Fam.Data BRFGA1
IOL	15Kcy / ΔTj ≥ 100°C	Fam.Data BVJJA1 + BVJ7A1	Fam.Data BVJJA1 + BVJ7A1 + BRGNA1	77 x 2 Lots + Fam.Data BVJ7A1	Fam.Data BVJJA1 + BVJ7A1	77 x 3 Lots	Fam.Data BRFGA1	Fam.Data BRFGA1	Fam.Data BRFGA1
ESD	ESD HBM/CDM Characterization	1 Lots	1 Lots	1 Lots	1 Lots	1 Lots	1 Lots	1 Lots	1 Lots
DPA	Devices after TC and H3TRB	Fam.Data BVJJA1 + BVJ7A1	Fam.Data BVJJA1 + BVJ7A1	1 Lots	Fam.Data BVJJA1 + BVJ7A1	1 Lot	Fam.Data BRFGA1	Fam.Data BRFGA1	Fam.Data BRFGA1



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Reliability Test Item	Test Condition	BRIGA1	BRJNA2	BVJJA1	BRICA1	BRGNA1	BRFCA1	BRF9A1	BRF5A1
DRB	1000h @ Ta=25°C, Vdspeak=100%BVDss, dVds/dt ~50V/ns, Duty Cycle 50%, Freq. 25KHz	Fam. Data BVJJA1 + BVJ7A1 HU3PAK	Fam. Data BVJJA1 + BVJ7A1 HU3PAK	Fam. Data BVJJA1 + BVJ7A1 HU3PAK	Fam. Data BVJJA1 + BVJ7A1 HU3PAK	Fam. Data BVJJA1 + BVJ7A1 + BRFG HU3PAK	Fam. Data BVJJA1 + BVJ7A1 + BRFG HU3PAK	Fam. Data BVJJA1 + BVJ7A1 + BRFG HU3PAK	Fam. Data BVJJA1 + BVJ7A1 + BRFG HU3PAK
DGS	VGS Range = -5/18V, minimum requirement conditions according to AQG324	Fam. Data BRJOA1 TO247-4	Fam. Data BRJOA1 TO247-4	Fam. Data BRJOA1 TO247-4	Fam. Data BRJOA1 TO247-4	Fam. Data BRJOA1 TO247-4	Fam. Data BRFGA1 STPAK	Fam. Data BRFGA1 STPAK	Fam. Data BRFGA1 STPAK
Dyn HV H3TRB	Ta=85°C, 85%HR Vdspeak=80%BVDss, dVds/dt ≥ 30V/ns, Duty Cycle 50%, Freq.= 15÷25 kHz	Fam. Data BRJOA1 TO247-4	Fam. Data BRJOA1 TO247-4	Fam. Data BRJOA1 TO247-4	Fam. Data BRJOA1 TO247-4	Fam. Data BRJOA1 TO247-4+ BRFGA1 HU3PAK	Fam. Data BRJOA1 TO247-4 + BRFGA1 HU3PAK	Fam. Data BRFGA1 STPAK+ BRFGA1 HU3PAK	Fam. Data BRFGA1 STPAK+ BRFGA1 HU3PAK

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